NSN 5962-01-341-5891

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-341-5891

Overall Length:
1.060 inches
Overall Height:
0.400 inches
Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.130 inches and 0.185 inches
Maximum Power Dissipation Rating:
1.1 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and high impedance and w/clock and monolithic and programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
180.00 milliamperes supply
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
50.00 nanoseconds propagation delay time, high to low level output and 50.00 nanoseconds propagation delay time, low to high level
output
Memory Device Type:
Programmable
Test Data Document:
00000 mil eta donte la planta de la planta en especial de la planta d

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

NSN 5962-01-341-5891

Memory Microcircuit - Page 2 of 2

AeroBase Group

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0